74AVC4T774

4-bit dual supply translating transceiver; 3-state

Rev. 2 — 2 January 2023

Product data sheet

1. General description

The 74AVC4T774 is a 4-bit, dual supply transceiver that enables bidirectional level translation. It features eight 1-bit input-output ports (An and Bn), four direction control inputs (DIR1, DIR2, DIR3 and DIR4), an output enable input (\overline{OE}) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins An, \overline{OE} and DIRn are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A HIGH on DIRn allows transmission from An to Bn and a LOW on DIRn allows transmission from Bn to An. The output enable input (\overline{OE}) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both An and Bn are in the high-impedance OFF-state.

2. Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM: ANSI/ESDA/Jedec JS-001 Class 3B exceeds 8000 V
 - CDM: ANSI/ESDA/Jedec JS-002 Class C3 exceeds 1500 V
- Maximum data rates:
 - 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
 - 200 Mbit/s (≥ 1.1 V to 3.3 V translation)
 - 200 Mbit/s (≥ 1.1 V to 2.5 V translation)
 - 200 Mbit/s (≥ 1.1 V to 1.8 V translation)
 - 150 Mbit/s (≥ 1.1 V to 1.5 V translation)
 - 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- · Latch-up performance exceeds 100 mA per JESD 78 Class II
- · Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

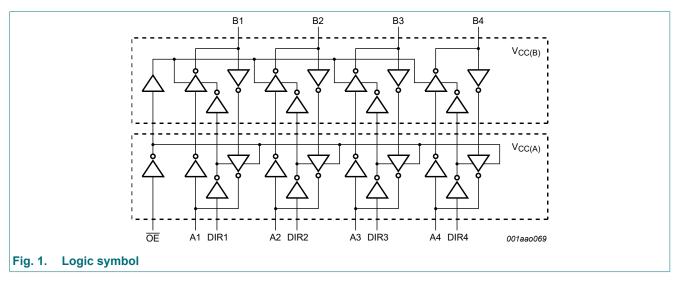
Type number	Package								
	Temperature range	Name	Description	Version					
74AVC4T774BQ	-40 °C to +125 °C		plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1					
74AVC4T774GU	-40 °C to +125 °C	XQFN16	plastic, extremely thin quad flat package; no leads; 16 terminals; body 1.80 × 2.60 × 0.50 mm	SOT1161-1					

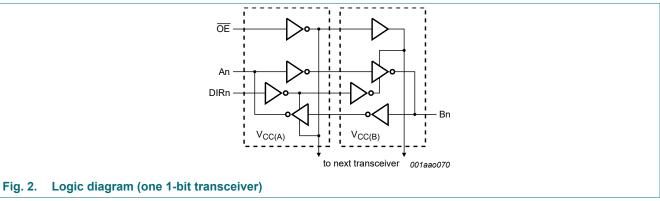
4. Marking

Table 2. Marking codes

Type number	Marking code
74AVC4T774BQ	C4T774
74AVC4T774GU	B77

5. Functional diagram

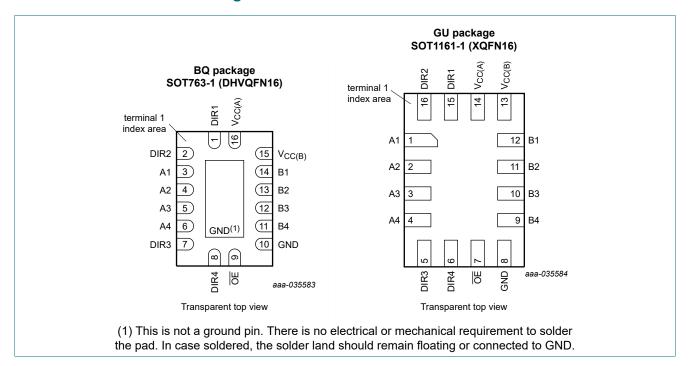




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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT763-1	SOT1161-1	
V _{CC(A)}	16	14	supply voltage A (An, $\overline{\text{OE}}$ and DIRn inputs are referenced to $V_{\text{CC(A)}}$)
DIR1, DIR2, DIR3, DIR4	1, 2, 7, 8	15, 16, 5, 6	direction control input
A1, A2, A3, A4	3, 4, 5, 6	1, 2, 3, 4	data input or output
GND	10	8	ground (0 V)
B1, B2, B3, B4	14, 13, 12, 11	12, 11, 10, 9	data input or output
ŌĒ	9	7	output enable input (active LOW)
V _{CC(B)}	15	13	supply voltage B (Bn pins are referenced to $V_{\text{CC(B)}}$)

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7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

The An, DIRn and \overline{OE} input circuit is referenced to $V_{CC(A)}$; The Bn input circuit is referenced to $V_{CC(B)}$.

Supply voltage	Input			Input/output			
V _{CC(A)} , V _{CC(B)}	ŌĒ	DIR1	DIR2	DIR3	DIR4	An	Bn
0.8 V to 3.6 V	L	L	Х	Х	Х	A1 = B1	input B1
0.8 V to 3.6 V	L	Н	Х	Х	Х	input A1	B1 = A1
0.8 V to 3.6 V	L	Х	L	Х	Х	A2 = B2	input B2
0.8 V to 3.6 V	L	Х	Н	Х	Х	input A2	B2 = A2
0.8 V to 3.6 V	L	Х	Х	L	Х	A3 = B3	input B3
0.8 V to 3.6 V	L	Х	Х	Н	Х	input A3	B3 = A3
0.8 V to 3.6 V	L	Х	Х	Х	L	A4 = B4	input B4
0.8 V to 3.6 V	L	Х	Х	Х	Н	input A4	B4 = A4
0.8 V to 3.6 V	Н	Х	Х	Х	Х	Z	Z
GND [1]	X	X	X	Х	Х	Z	Z

^[1] If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			-0.5	+4.6	V
V _{CC(B)}	supply voltage B			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mΑ
VI	input voltage		[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V		-50	-	mΑ
Vo	output voltage	Active mode [1][2	2][3]	-0.5	V _{CCO} + 0.5	V
		Suspend or 3-state mode	[1]	-0.5	+4.6	V
Io	output current	V _O = 0 V to V _{CCO}	[2]	-	±50	mΑ
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}		-	100	mΑ
I _{GND}	ground current			-100	-	mΑ
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C				
		SOT763-1 (DHVQFN16)	[4]	-	500	mW
		SOT1161-1 (XQFN16)		-	250	mW

^[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

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^[2] V_{CCO} is the supply voltage associated with the output port.

^[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

^[4] For SOT763-1 (DHVQFN16) package: P_{tot} derates linearly with 11.2 mW/K above 106 °C.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		0.8	3.6	V
V _{CC(B)}	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode [1]	0	V _{cco}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$ [2]	-	10	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

10. Static characteristics

Table 7. Typical static characteristics at T_{amb} = 25 °C

V_{CCI} is the supply voltage associated with the data input port.

*V*_{CCO} is the supply voltage associated with the output port.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}					
	output voltage	$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.69	-	V
V _{OL} LOW-level		$V_I = V_{IH}$ or V_{IL}					
	output voltage	$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.07	-	V
l _l	input leakage current	DIRn, \overline{OE} input; $V_I = 0 \text{ V or } 3.6 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$		-	±0.025	±0.25	μΑ
02	OFF-state output current	A or B port; $V_O = 0 \text{ V}$ or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$ [1]	-	±0.5	±2.5	μΑ
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ [1 $V_{CC(B)} = 0 \text{ V}$		-	±0.5	±2.5	μΑ
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 0 \text{ V};$ [1 $V_{CC(B)} = 3.6 \text{ V}$		-	±0.5	±2.5	μΑ
I _{OFF}	power-off leakage	A port; V_I or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V		-	±0.1	±1	μΑ
	current	B port; V_I or $V_O = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V		-	±0.1	'	μΑ
C _I	input capacitance	DIRn, \overline{OE} input; $V_I = 0 \text{ V or } 3.3 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$		-	2.0	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_O = 3.3 \text{ V}$ or 0 V; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$		-	4.0	-	pF

^[1] For I/O ports, the parameter $I_{\mbox{\scriptsize OZ}}$ includes the input leakage current.

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^[2] V_{CCI} is the supply voltage associated with the input port.

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Table 8. Static characteristics

 V_{CCI} is the supply voltage associated with the data input port.

V_{CCO} is the supply voltage associated with the output port.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions	-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V _{IH}	HIGH-level	data input					
	input voltage	V _{CCI} = 0.8 V	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	2	-	V
		DIRn, OE input					
		V _{CC(A)} = 0.8 V	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		V _{CC(A)} = 1.1 V to 1.95 V	0.65V _{CC(A)}	-	0.65V _{CC(A)}	-	V
		V _{CC(A)} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CC(A)} = 3.0 V to 3.6 V	2	-	2	-	٧
V_{IL}	LOW-level	data input					
	input voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
		DIRn, OE input					
		V _{CC(A)} = 0.8 V	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	٧
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
		V _{CC(A)} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CC(A)} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
V _{OH}	HIGH-level	V _I = V _{IH} or V _{IL}					
	output voltage	$I_O = -100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	V
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_O = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_O = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_O = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V

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Symbol	Parameter	Conditions		-40 °C t	o +85 °C	-40 °C to	Unit	
				Min	Max	Min	Max	
V _{OL}	LOW-level	V _I = V _{IH} or V _{IL}						
	output voltage	$I_O = 100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$		-	0.1	-	0.1	V
		$I_O = 3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$		-	0.25	-	0.25	V
		$I_O = 6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-	0.35	-	0.35	V
		$I_O = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$		-	0.45	-	0.45	V
		$I_O = 9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$		-	0.55	-	0.55	V
		I_O = 12 mA; $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$		-	0.7 - 0.7	V		
I _I	input leakage current	DIRn, \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V		-	±1	-	±5	μA
l _{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[1]	-	±5	-	±30	μA
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}$	[1]	-	±5	-	±30	μA
		suspend mode B port; [1] $V_O = 0 \text{ V or } V_{CC(G)}; V_{CC(A)} = 0 \text{ V};$ $V_{CC(B)} = 3.6 \text{ V}$		-	±5	-	±30	μA
I _{OFF}	power-off leakage	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V		-	±5	-	±30	μΑ
	current	B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V		-	±5	-	±30	μA

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Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	Unit	
			Min	Max	Min	Max	
I _{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		V _{CC(A)} = 0.8 V to 3.6 V; V _{CC(B)} = 0.8 V to 3.6 V	-	10	-	55	μA
		V _{CC(A)} = 1.1 V to 3.6 V; V _{CC(B)} = 1.1 V to 3.6 V	-	8	-	50	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	-	8	-	50	μA
		V _{CC(A)} = 0 V; V _{CC(B)} = 3.6 V	-2	-	-12	-	μA
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μA
		V _{CC(A)} = 1.1 V to 3.6 V; V _{CC(B)} = 1.1 V to 3.6 V	-	8	-	50	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	-2	-	-12	-	μΑ
		V _{CC(A)} = 0 V; V _{CC(B)} = 3.6 V	-	8	-	50	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	20	-	70	μА
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V	-	16	-	65	μА
ΔI _{CC}	additional supply current	$V_1 = 3.0 \text{ V}; V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	-	500	-	650	μA

^[1] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 9. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

V _{CC(A)}	V _{CC(B)}		<u> </u>					Unit
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

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11. Dynamic characteristics

Table 10. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25$ °C

Voltages are referenced to GND (ground = 0 V). [1] [2]

Symbol	Parameter	Conditions			V _{CC(A)} :	= V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD}	power dissipation capacitance	A port: (direction An to Bn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction An to Bn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction Bn to An); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF
		A port: (direction Bn to An); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction An to Bn); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF
		B port: (direction An to Bn); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction Bn to An); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		B port: (direction Bn to An); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$$\begin{split} &\Sigma(C_L \times V_{CC}^{-2} \times f_o) = \text{sum of the outputs.} \\ [2] \quad &f_i = 10 \text{ MHz; } V_i = \text{GND to } V_{CC}; \, t_r = t_f = 1 \text{ ns; } C_L = 0 \text{ pF; } R_L = \infty \Omega. \end{split}$$

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Table 11. Typical dynamic characteristics at $V_{CC(A)}$ = 0.8 V and T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5; for waveforms see Fig. 3 and Fig. 4. [1]

Symbol	Parameter	Conditions	V _{CC(B)}						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	t _{pd} propagation delay	An to Bn	14.5	7.3	6.5	6.2	5.9	6.0	ns
		Bn to An	14.5	12.7	12.4	12.3	12.1	12.0	ns
t _{dis}	disable time	OE to An	14.3	14.3	14.3	14.3	14.3	14.3	ns
		OE to Bn	17.0	9.9	9.0	9.4	9.0	9.7	ns
t _{en}	enable time	OE to An	18.2	18.2	18.2	18.2	18.2	18.2	ns
		OE to Bn	19.2	10.7	9.8	9.6	9.7	10.2	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 12. Typical dynamic characteristics at $V_{CC(B)}$ = 0.8 V and T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5; for waveforms see Fig. 3 and Fig. 4. [1]

Symbol	Parameter	Conditions	V _{CC(A)}							
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V		
t _{pd}	propagation delay	An to Bn	14.5	12.7	12.4	12.3	12.1	12.0	ns	
		Bn to An	14.5	7.3	6.5	6.2	5.9	6.0	ns	
t _{dis}	disable time	OE to An	14.3	5.5	4.1	4.0	3.0	3.5	ns	
		OE to Bn	17.0	13.8	13.4	13.1	12.9	12.7	ns	
t _{en}	enable time	OE to An	18.2	5.6	4.0	3.2	2.4	2.2	ns	
		OE to Bn	19.2	14.6	14.1	13.9	13.7	13.6	ns	

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

4-bit dual supply translating transceiver; 3-state

Table 13. Dynamic characteristics for temperature range -40 °C to +85 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5; for waveforms see Fig. 3 and Fig. 4. [1]

Symbol	Parameter	Conditions	V _{CC(B)}									Unit	
			1.2 V ± 0.1 V		1.5 V ± 0.1 V 1.8 V ± 0.1				2.5 V	± 0.2 V	3.3 V ± 0.3 V		-
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	1
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	An to Bn	2.0	10.5	1.3	7.8	1.2	6.9	1.0	5.9	0.8	5.7	ns
•	delay	Bn to An	2.0	10.5	1.5	9.9	1.5	9.7	1.4	9.4	1.4	9.3	ns
t _{dis}	disable time	OE to An	2.0	10.0	2.0	10.0	2.0	10.0	2.0	10.0	2.0	10.0	ns
		OE to Bn	2.0	11.1	2.0	8.6	1.0	8.0	0.7	7.0	1.0	8.0	ns
t _{en}	enable time	OE to An	2.0	13.5	2.0	13.5	2.0	13.5	2.0	13.5	2.0	13.5	ns
		OE to Bn	2.0	15.0	2.0	11.0	2.0	9.4	1.0	7.8	1.0	7.4	ns
V _{CC(A)} =	1.4 V to 1.6 V		1		ı						1		
t _{pd}	propagation	An to Bn	1.5	9.9	1.0	7.1	1.0	6.0	0.5	4.8	0.5	4.3	ns
	delay	Bn to An	1.3	7.8	1.0	7.1	0.9	6.9	0.8	6.6	0.6	6.5	ns
t _{dis}	disable time	OE to An	1.0	6.0	1.0	6.0	1.0	6.0	1.0	6.0	1.0	6.0	ns
		OE to Bn	2.0	10.2	1.5	7.5	0.9	7.2	0.4	6.2	0.4	6.1	ns
t _{en}	enable time	OE to An	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	ns
		OE to Bn	2.0	14.4	1.4	7.9	1.3	7.7	1.1	6.4	1.1	5.6	ns
V _{CC(A)} =	1.65 V to 1.95	V	•									'	
t _{pd}	propagation	An to Bn	1.5	9.7	0.9	6.9	0.8	5.7	0.5	4.5	0.3	4.0	ns
	delay	Bn to An	1.2	6.9	1.0	6.0	0.8	5.7	0.5	5.5	0.5	5.3	ns
t _{dis}	disable time	OE to An	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	ns
		OE to Bn	2.0	9.9	1.5	7.0	0.8	6.9	0.2	5.8	0.2	5.9	ns
t _{en}	enable time	OE to An	1.0	6.7	1.0	6.7	1.0	6.7	1.0	6.7	1.0	6.7	ns
		OE to Bn	1.5	13.9	1.2	7.2	1.2	6.9	0.8	5.4	0.6	5.0	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	An to Bn	1.4	9.4	0.8	6.6	0.5	5.5	0.4	4.2	0.2	3.7	ns
	delay	Bn to An	1.0	5.9	0.5	4.8	0.5	4.5	0.4	4.2	0.3	3.9	ns
t _{dis}	disable time	OE to An	0.2	4.0	0.2	4.0	0.2	4.0	0.2	4.0	0.2	4.0	ns
		OE to Bn	2.0	9.3	1.5	6.7	0.7	6.3	0.2	5.0	0.2	5.7	ns
t _{en}	enable time	OE to An	0.6	4.5	0.6	4.5	0.6	4.5	0.6	4.5	0.6	4.5	ns
		OE to Bn	1.5	13.6	1.0	6.8	1.0	6.0	8.0	4.6	0.6	4.2	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	An to Bn	1.4	9.3	0.6	6.5	0.5	5.3	0.3	3.9	0.2	3.5	ns
	delay	Bn to An	8.0	5.7	0.5	4.3	0.3	4.0	0.2	3.7	0.2	3.5	ns
t _{dis}	disable time	OE to An	0.2	4.5	0.2	4.5	0.2	4.5	0.2	4.5	0.2	4.5	ns
		OE to Bn	2.0	9.0	1.5	6.4	0.7	6.1	0.2	4.8	0.2	5.6	ns
t _{en}	enable time	OE to An	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	ns
		OE to Bn	1.5	13.4	1.0	6.7	1.0	5.9	0.7	4.4	0.5	4.0	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

4-bit dual supply translating transceiver; 3-state

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5; for waveforms see Fig. 3 and Fig. 4. [1]

Symbol	Parameter	Conditions	V _{CC(B)}									Unit	
			1.2 V	± 0.1 V	1.5 V :	± 0.1 V	1.8 V ± 0.15 V		2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	An to Bn	2.0	12.1	1.3	9.0	1.2	8.0	1.0	6.8	0.8	6.6	ns
	delay	Bn to An	2.0	12.1	1.5	11.4	1.5	11.2	1.4	10.9	1.4	10.7	ns
t _{dis}	disable time	OE to An	2.0	11.5	2.0	11.5	2.0	11.5	2.0	11.5	2.0	11.5	ns
		OE to Bn	2.0	12.8	2.0	9.9	1.0	9.2	0.7	8.1	1.0	9.2	ns
t _{en}	enable time	OE to An	2.0	15.6	2.0	15.6	2.0	15.6	2.0	15.6	2.0	15.6	ns
		OE to Bn	2.0	17.3	2.0	12.7	2.0	10.9	1.0	9.0	1.0	8.6	ns
V _{CC(A)} =	1.4 V to 1.6 V						ı			1	1		
t _{pd}	propagation	An to Bn	1.5	11.4	1.0	8.2	1.0	6.9	0.5	5.6	0.5	5.0	ns
	delay	Bn to An	1.3	9.0	1.0	8.2	0.9	8.0	0.8	7.6	0.6	7.5	ns
t _{dis}	disable time	OE to An	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	ns
		OE to Bn	2.0	11.8	1.5	8.7	0.9	8.3	0.4	7.2	0.4	7.1	ns
t _{en}	enable time	OE to An	1.0	8.7	1.0	8.7	1.0	8.7	1.0	8.7	1.0	8.7	ns
		OE to Bn	2.0	16.6	1.4	9.1	1.3	8.9	1.1	7.4	1.1	6.5	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd}	propagation delay	An to Bn	1.5	11.2	0.9	8.0	0.8	6.6	0.5	5.2	0.3	4.6	ns
		Bn to An	1.2	8.0	1.0	6.9	0.8	6.6	0.5	6.4	0.5	6.1	ns
t _{dis}	disable time	OE to An	0.5	6.6	0.5	6.6	0.5	6.6	0.5	6.6	0.5	6.6	ns
		OE to Bn	2.0	11.4	1.5	8.1	0.8	8.0	0.2	6.7	0.2	6.8	ns
t _{en}	enable time	OE to An	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	ns
		OE to Bn	1.5	16.0	1.2	8.3	1.2	8.0	0.8	6.3	0.6	5.8	ns
V _{CC(A)} =	2.3 V to 2.7 V		'	'	'	'	'	'	'	'	'	'	'
t _{pd}	propagation	An to Bn	1.4	10.9	0.8	7.6	0.5	6.4	0.4	4.9	0.2	4.3	ns
	delay	Bn to An	1.0	6.8	0.5	5.6	0.5	5.2	0.4	4.9	0.3	4.5	ns
t _{dis}	disable time	OE to An	0.2	4.6	0.2	4.6	0.2	4.6	0.2	4.6	0.2	4.6	ns
		OE to Bn	2.0	10.7	1.5	7.8	0.7	7.3	0.2	5.8	0.2	6.6	ns
t _{en}	enable time	OE to An	0.6	5.2	0.6	5.2	0.6	5.2	0.6	5.2	0.6	5.2	ns
		OE to Bn	1.5	15.7	1.0	7.9	1.0	6.9	0.8	5.3	0.6	4.9	ns
V _{CC(A)} =	3.0 V to 3.6 V			'		'	'		'		<u> </u>	'	'
t _{pd}	propagation	An to Bn	1.4	10.7	0.6	7.5	0.5	6.1	0.3	4.5	0.2	4.1	ns
	delay	Bn to An	0.8	6.6	0.5	5.0	0.3	4.6	0.2	4.3	0.2	4.1	ns
t _{dis}	disable time	OE to An	0.2	5.2	0.2	5.2	0.2	5.2	0.2	5.2	0.2	5.2	ns
		OE to Bn	2.0	10.4	1.5	7.4	0.7	7.1	0.2	5.6	0.2	6.5	ns
t _{en}	enable time	OE to An	0.5	4.6	0.5	4.6	0.5	4.6	0.5	4.6	0.5	4.6	ns
		OE to Bn	1.5	15.5	1.0	7.8	1.0	6.8	0.7	5.1	0.5	4.6	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

4-bit dual supply translating transceiver; 3-state

11.1. Waveforms and test circuit

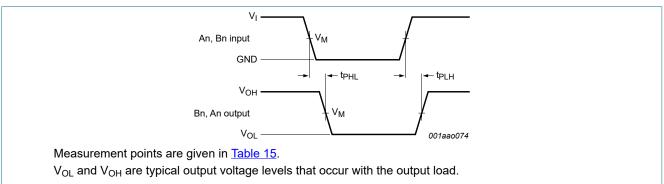


Fig. 3. The data input (An, Bn) to output (Bn, An) propagation delay times

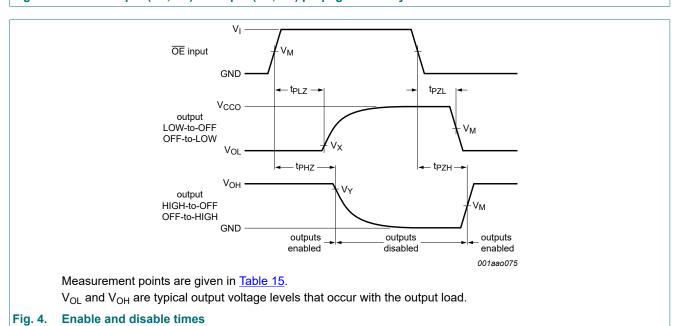


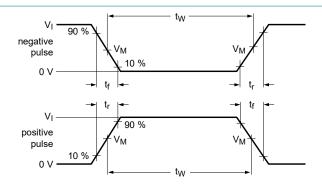
Table 15. Measurement points

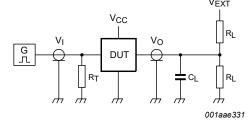
Table 13. Measurement points									
Supply voltage	Input [1]	Output [2]	Output [2]						
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y					
0.8 V to 1.6 V	0.5 × V _{CCI}	0.5 × V _{CCO}	V _{OL} + 0.1 V	V _{OH} - 0.1 V					
1.65 V to 2.7 V	0.5 × V _{CCI}	0.5 × V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V					
3.0 V to 3.6 V	0.5 × V _{CCI}	0.5 × V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V					

^[1] V_{CCI} is the supply voltage associated with the data input port.

^[2] V_{CCO} is the supply voltage associated with the output port.

4-bit dual supply translating transceiver; 3-state





Test data is given in Table 16.

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_{T} = Termination resistance should be equal to the output impedance Z_{o} of the pulse generator;

V_{EXT} = External voltage for measuring switching times.

Fig. 5. Test circuit for measuring switching times

Table 16. Test data

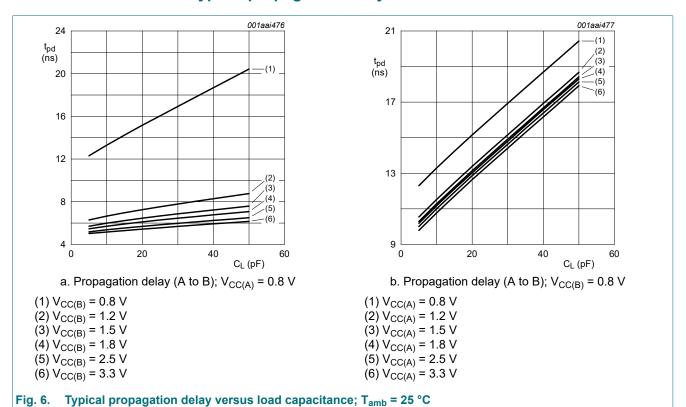
Supply voltage	Input		Load		V _{EXT}		
$V_{CC(A)}, V_{CC(B)}$	V _I [1]	Δt/ΔV [2]	CL	R _L	t_{PLH} , t_{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]
0.8 V to 1.6 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2 × V _{CCO}
1.65 V to 2.7 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2 × V _{CCO}
3.0 V to 3.6 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2 × V _{CCO}

- [1] V_{CCI} is the supply voltage associated with the data input port.
- [2] dV/dt ≥ 1.0 V/ns.
- [3] V_{CCO} is the supply voltage associated with the output port.

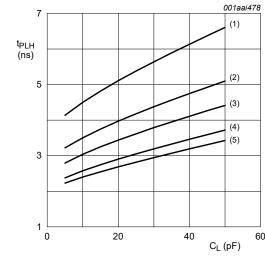
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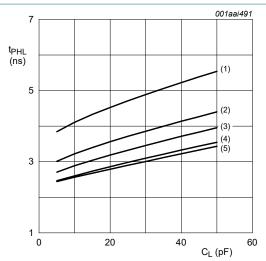
4-bit dual supply translating transceiver; 3-state

11.2. Typical propagation delay characteristics

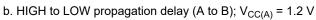


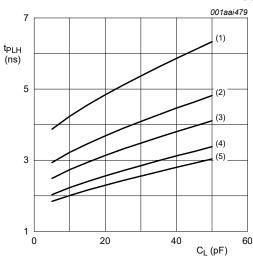
4-bit dual supply translating transceiver; 3-state

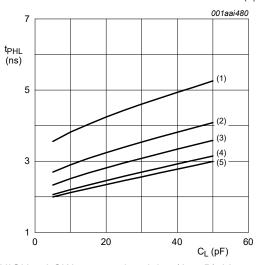




a. LOW to HIGH propagation delay (A to B); $V_{CC(A)} = 1.2 \text{ V}$





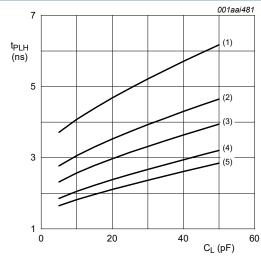


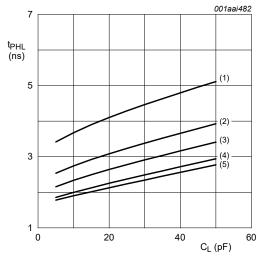
c. LOW to HIGH propagation delay (A to B); $V_{CC(A)} = 1.5 \text{ V}$ d. HIGH to LOW propagation delay (A to B); $V_{CC(A)} = 1.5 \text{ V}$

- (1) $V_{CC(B)} = 1.2 \text{ V}$
- (2) $V_{CC(B)} = 1.5 \text{ V}$
- (3) $V_{CC(B)} = 1.8 \text{ V}$
- (4) $V_{CC(B)} = 2.5 \text{ V}$
- $(5) V_{CC(B)} = 3.3 V$

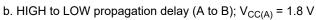
Fig. 7. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

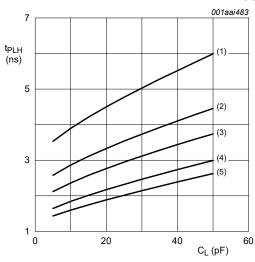
4-bit dual supply translating transceiver; 3-state

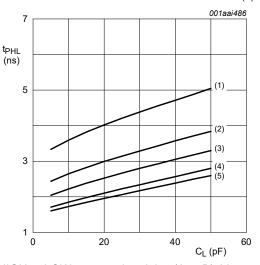




a. LOW to HIGH propagation delay (A to B); $V_{CC(A)}$ = 1.8 V







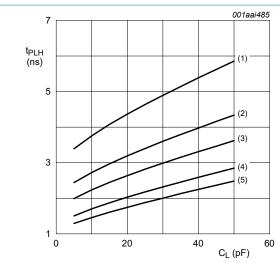
c. LOW to HIGH propagation delay (A to B); $V_{CC(A)} = 2.5 \text{ V}$ d. HIGH to LOW propagation delay (A to B); $V_{CC(A)} = 2.5 \text{ V}$

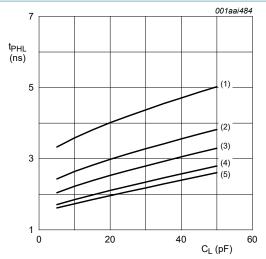
- (1) $V_{CC(B)} = 1.2 \text{ V}$
- (2) $V_{CC(B)} = 1.5 \text{ V}$
- (3) $V_{CC(B)} = 1.8 \text{ V}$
- (4) $V_{CC(B)} = 2.5 \text{ V}$
- $(5) V_{CC(B)} = 3.3 V$

Fig. 8. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

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4-bit dual supply translating transceiver; 3-state





- a. LOW to HIGH propagation delay (A to B); $V_{CC(A)} = 3.3 \text{ V}$ b. HIGH to LOW propagation delay (A to B); $V_{CC(A)} = 3.3 \text{ V}$
 - (1) $V_{CC(B)} = 1.2 \text{ V}$
 - (2) $V_{CC(B)} = 1.5 \text{ V}$
 - (3) $V_{CC(B)} = 1.8 \text{ V}$
 - (4) $V_{CC(B)} = 2.5 \text{ V}$
 - (5) $V_{CC(B)} = 3.3 \text{ V}$
- Fig. 9. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

4-bit dual supply translating transceiver; 3-state

12. Package outline

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

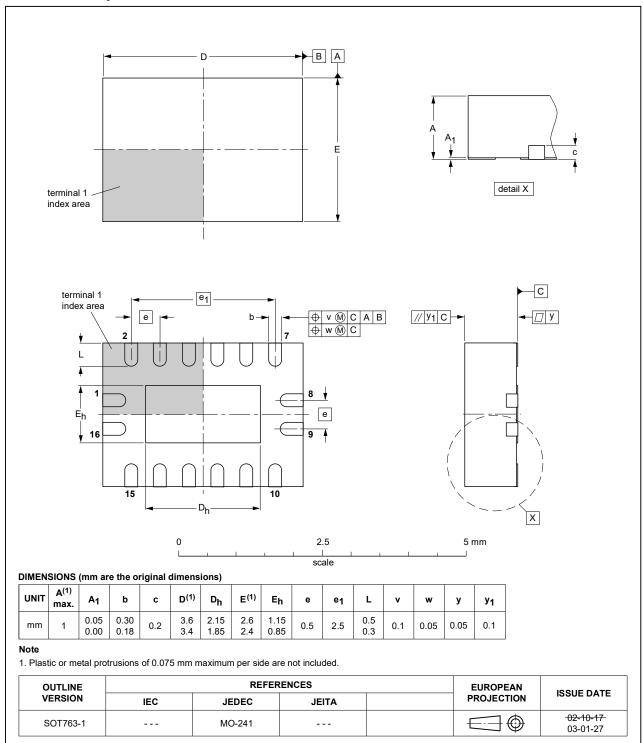


Fig. 10. Package outline SOT763-1 (DHVQFN16)

4-bit dual supply translating transceiver; 3-state

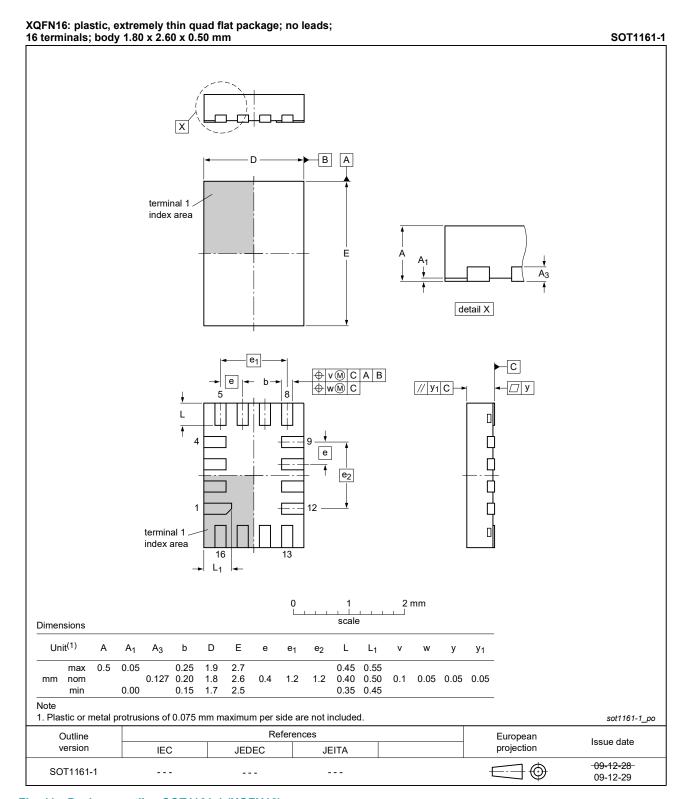


Fig. 11. Package outline SOT1161-1 (XQFN16)

4-bit dual supply translating transceiver; 3-state

13. Abbreviations

Table 17. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model

14. Revision history

Table 18. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC4T774 v.2	20230102	Product data sheet	-	74AVC4T774 v.1
Modifications:	Section 2 upSection 8: D	odated. Perating values for P _{tot} total	power dissipation	n updated.
74AVC4T774 v.1	20170925	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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